Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

Panasonic

MOS FET FC8V22150L

FC8V22150L

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

Features

- Low drain-source ON resistance:Rds(on) typ. = 9.0 mΩ(VGS = 4.5 V)
- Built-in gate resistor
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 53

Packaging

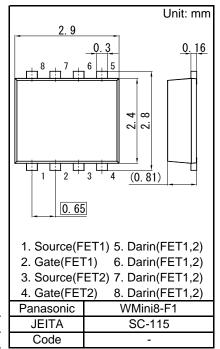
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

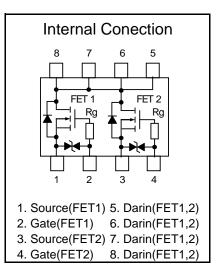
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source Voltage	VDS	24	V
Gate-source Voltage	VGS	±12	V
Drain Current (DC) ^{*2}	ID	12	А
Drain Current (Pulsed) *1	IDp	48	А
Total Power Dissipation	PD	2.0	W
Channel Temperature	Tch	150	С°
Storage Temperature Range	Tstg	-55 to +150	С°
Thermal resistance (ch-a)	Rth(ch-a)	125	°C/W

Note *1 t = 10 μ s, Duty Cycle \leq 1 %

*2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).







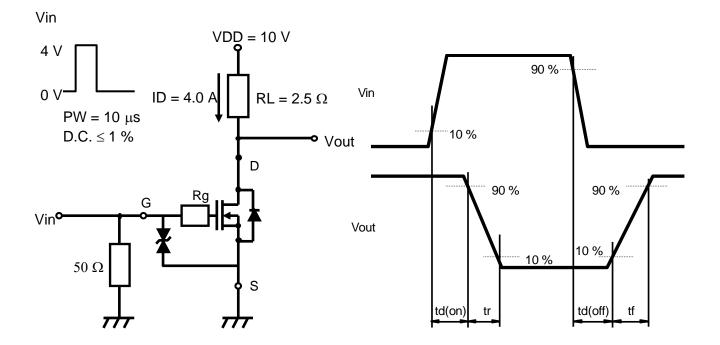
MOS FET FC8V22150L

■ Electrical Characteristics Ta = 25 °C ± 3 °C

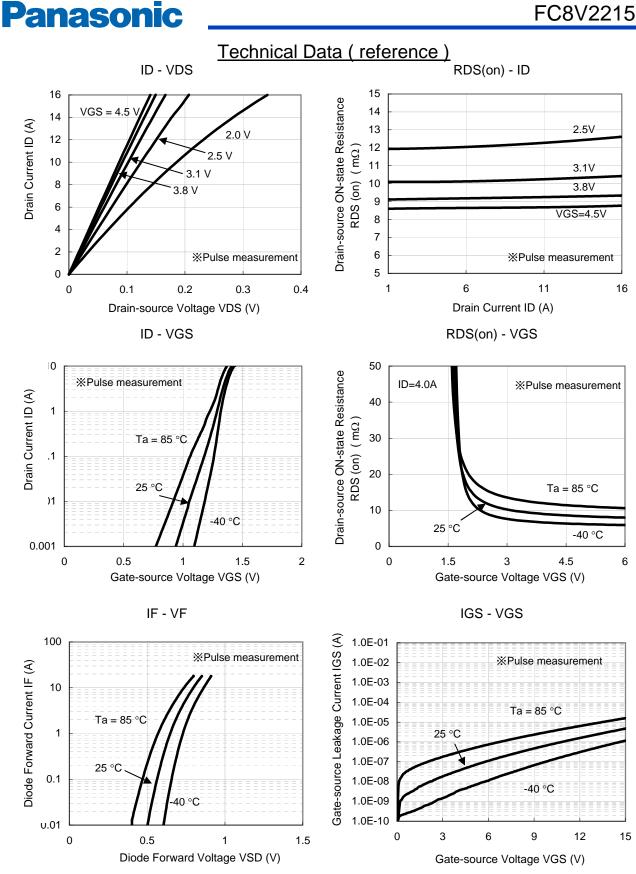
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	24			V
Zero Gate Voltage Drain Current	IDSS	VDS = 24 V, VGS = 0 V			1.0	μΑ
Gate-source Leakage Current	IGSS	$VGS = \pm 8 V, VSS = 0 V$			±1	μΑ
Gate-source Threshold Voltage	Vth	ID = 0.48 mA, VDS = 10 V	0.4	0.9	1.4	V
Drain-source On-state Resistance	RDS(on)1	ID = 4.0 A, VGS = 4.5 V	6.9	9.0	11.8	mΩ
	RDS(on)2	ID = 4.0 A, VGS = 3.8 V	6.9	9.5	12.9	
	RDS(on)3	ID = 4.0 A, VGS = 3.1 V	7.3	10.5	15.3	
	RDS(on)4	ID = 4.0 A, VGS = 2.5 V	7.6	12.2	20	
Body Diode Forward Voltage	VSD	IF = 4.0 A, VGS = 0 V		0.8	1.2	V
Input Capacitance ^{*1}	Ciss			1230		pF
Output Capacitance ^{*1}	Coss	VDS = 10 V, VGS = 0 V, f = 1 MHz		115		
Reverse Transfer Capacitance ^{*1}	Crss	[95		
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.45		
Rise Time ^{*1,*2}	tr	ID = 4.0 A		0.75		μS
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		3		
Fall Time *1,*2	tf	ID = 4.0 A		1.5		μS
Total Gate Charge ^{*1}	Qg	VDD = 10 V		11		
Gate-source Charge *1	Qgs	VGS = 0 to 4.0 V, ID = 8.0 A		4		nC
Gate-drain Charge ^{*1}	Qgd			2.5		

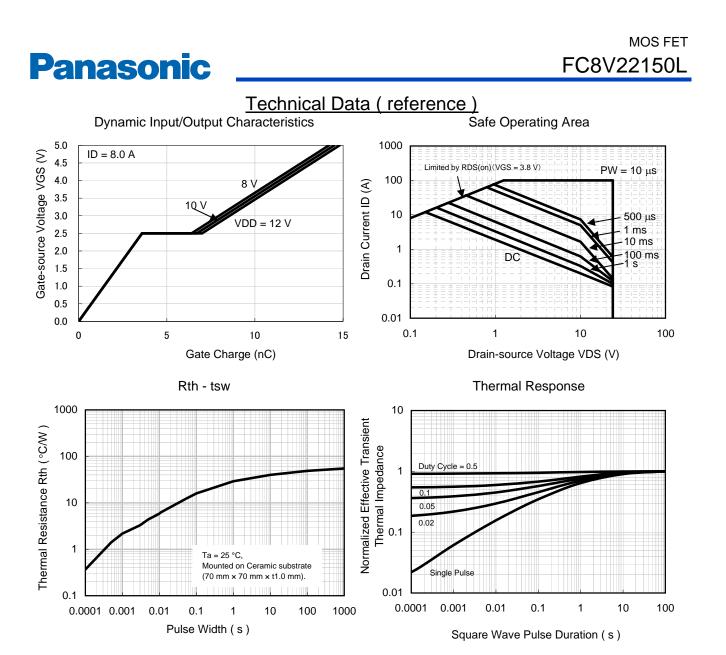
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. *1 Assured by design

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

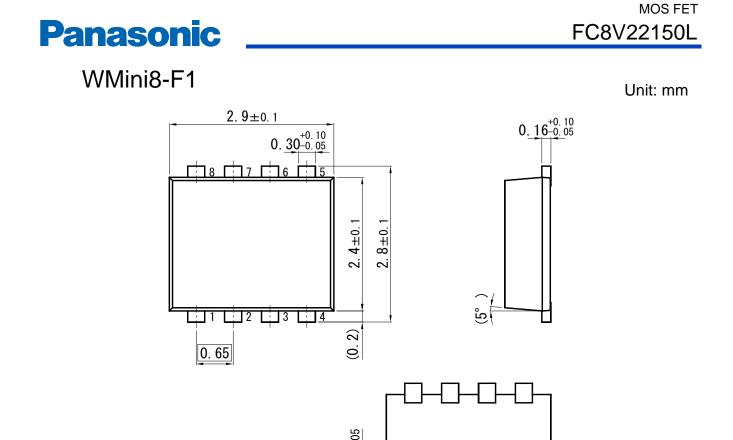


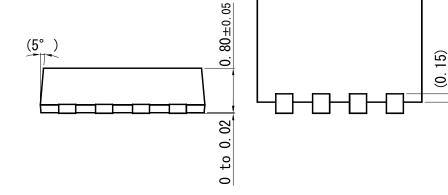




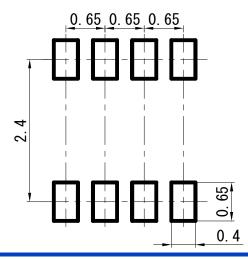


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Established : 2013-10-08 Revised : ###-##-##

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